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- (71) Applicant (for all designated States except US): SEMI-CONDUCTOR ENERGY LABORATORY CO., LTD. [JP/JP]; 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).
- (72) Inventor; and
- (75) Inventor/Applicant (for US only): YAMAZAKI, Shunpei [JP/JP]; c/o SEMICONDUCTOR ENERGY LABO-RATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

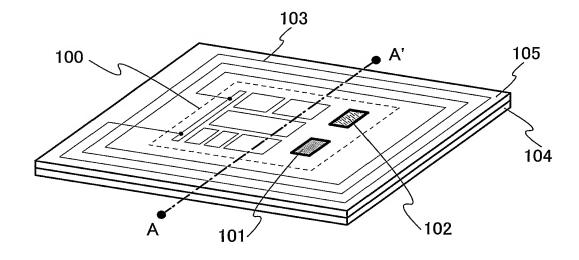
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(54) Title: ID CHIP AND IC CARD



(57) Abstract: The present invention provides an ID chip or an IC card in which the mechanical strength of an integrated circuit can be enhanced without suppressing a circuit scale. An ID chip or an IC card of the present invention has an integrated circuit in which a TFT (a thin film transistor) is formed from an insulated thin semiconductor film. Further, an ID chip or an IC card of the present invention has a light-emitting element and a light-receiving element each using a non-single-crystal thin film for a layer conducting photoelectric conversion. Such a light-emitting element or a light-receiving element may be formed consecutively to (integrally with) an integrated circuit or may be formed separately and attached to an integrated circuit.

